

1203 APD (Avalanche Photo Diode)

APD2001

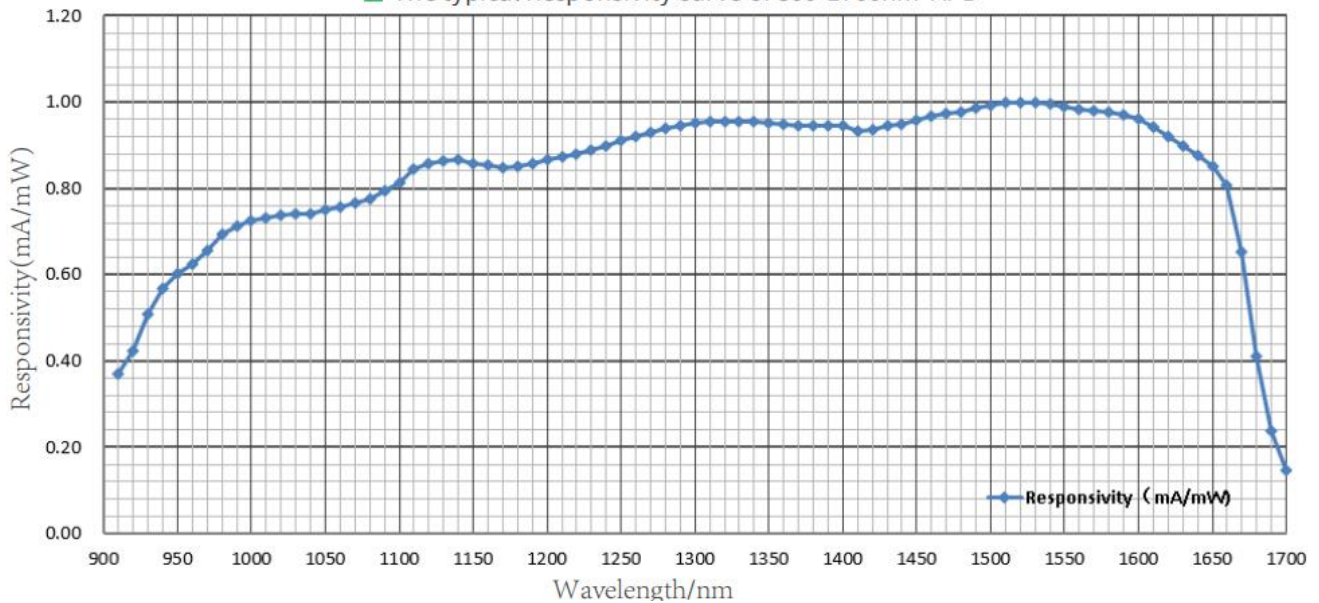
800 nm to 1700 nm InGaAs Avalanche Photodiode

USE IN

- Ultra Weak Optical Detecting
- Optical Sensor OTDR
- Laser Lidar
- Laser Range Finding
- High Resolution Optical Coherence Tomography
- Scientific Analysis and Experiment

Part No.	Photosurface (μm)	Response Wavelength (nm)	Responsivity (mA/mW@M=1)	Gain (1550 nm, 1 μW)	Reverse Breakdown Voltage (Id=10 μA)	Dark Current (nA@M=100)
APD2001-1	Φ30	800 to 1700	0.8@1550	M=10@Vbr-4 V M=20@Vbr-2 V	20 V to 50 V	0.5 nA @M=10
APD2001-2	Φ50	800 to 1700	0.9@1550	M=30@Vbr-1.2 V	44±4 V	0.8 nA @M=10
APD2001-3	Φ200	800 to 1700	0.9@1550 0.65@1064	M=10@Vbr-4 V M=20@Vbr-2 V	45±10 V	10 nA @M=10
APD2001-4	Φ500	800 to 1700	0.9@1550 0.65@1064	M=30@Vbr-1 V	45±10 V	130 nA @M=10

■ The typical Responsivity curve of 800-1700nm APD



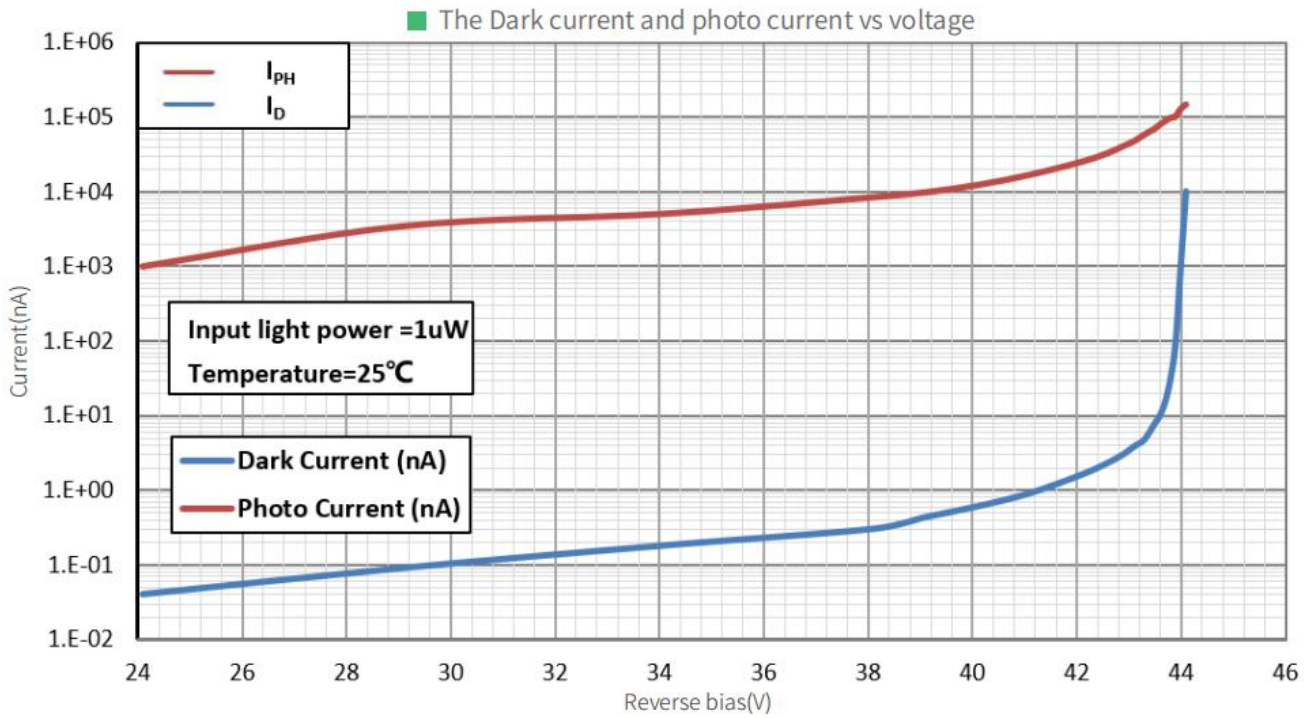
Order notes to our customers: The default parameters are as follows. For special needs, please contact sales.

1) Connector FC/APC, 900 μm, 1 m by default for all devices except for high power devices.

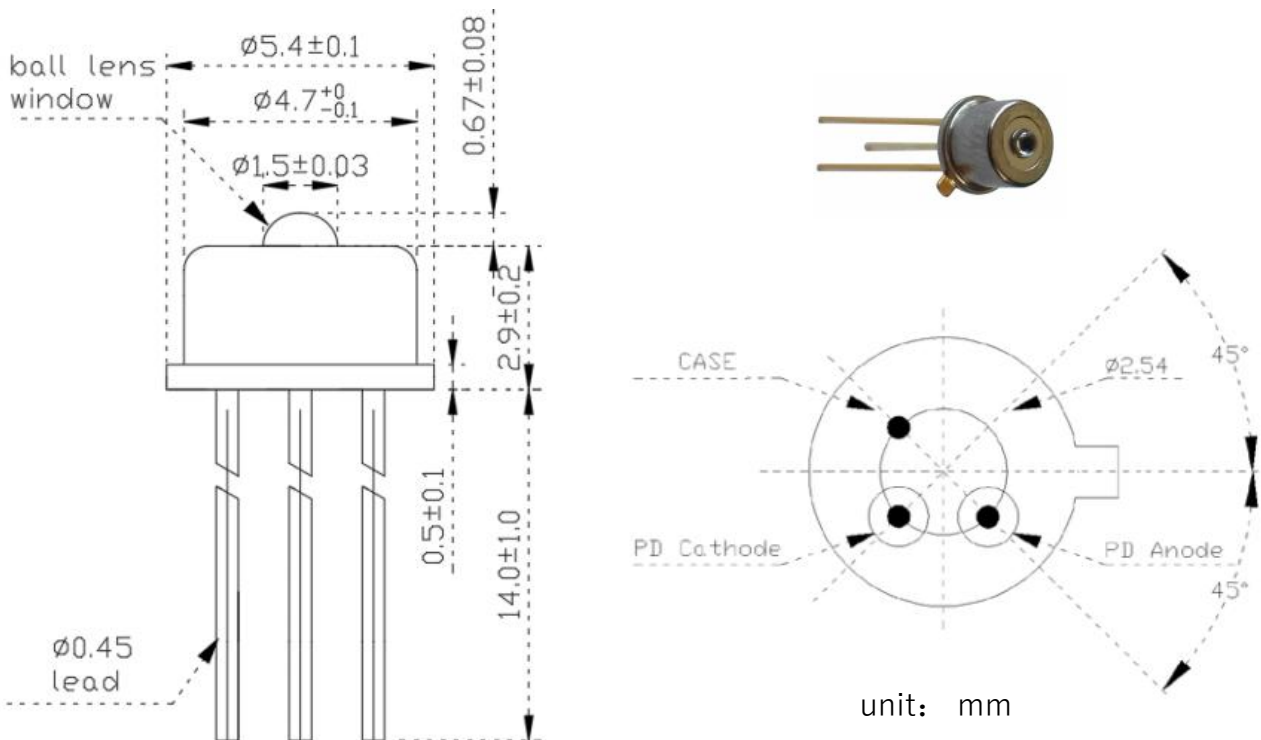
2) Slow axis working, fast axis blocked, connector key is aligned to slow axis by default for PM devices.

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MECHANICAL DRAWING



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